

EAST - [thinsearch15.wsp:1]

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Active

L1: (2) "6117750"

L2: (412523) semiconductor and substrate

L3: (101) L2 and (threading adj dislocation)

Failed

(27) (((semiconductor and gate) and isotropic) and (not a

(213) (((semiconductor and gate) and isotropic) and (not a

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Databases: USPAT, USPGPUB, EPO, JPO, DERWENT, IBM, TDB [Plurals] [Synonyms]

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L2 and (threading adj dislocation)

BRS form IS&R form Image Text

| | U | 1 | Document ID | Issue Date | Pages | Title | Current OR | Current XRel |
|----|-------------------------------------|--------------------------|----------------------|------------|-------|--|------------|--------------|
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| 2 | <input type="checkbox"/> | <input type="checkbox"/> | US 20010040244 A1 | | 10 | Relaxed InGaAs buffers | | |
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| 5 | <input type="checkbox"/> | <input type="checkbox"/> | US 20010031385 A1 | | 11 | Group III-V compound semiconductor and method of produ | | |
| 6 | <input type="checkbox"/> | <input type="checkbox"/> | US 20010030329 A1 | | 30 | Nitride compound semiconductor light emitting device and method for | | |
| 7 | <input type="checkbox"/> | <input type="checkbox"/> | US 20010026873 A1 | | 10 | METHOD FOR PRODUCING HIGH QUALITY HETEROEPITAX | | |
| 8 | <input type="checkbox"/> | <input type="checkbox"/> | US 20010024884 A1 | | 10 | Low threading dislocation density relaxed mismatched epilayers without | | |
| 9 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20010023946 A1 | | 11 | Crystal growth method for nitride semiconductor, nitride semiconducto | | |
| 10 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20010012678 A1 | | 31 | Method for the formation of semiconductor laver | | |

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- L1: (2) "6117750"
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- L4: (27) ((semiconductor and substrate) and lattice-mism)

Failed

- (27) (((semiconductor and gate) and isotropic) and (not &))
- (213) (((semiconductor and gate) and isotropic) and (not &))

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DBs: USPAT: US-PGPUB: EPO: JPO: DERWENT: IBM TDB

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((semiconductor and substrate) and lattice-mismatched) and multilayer

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| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 20010038655 A1 | | 39 | Semiconductor devices | | |
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| 3 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6222200 B1 | 20010424 | 13 | Photodetector with spectrally extended responsivity | 257/18 | 136/246 257/185 257/186 |
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| 5 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 6010937 A | 20000104 | 10 | Reduction of dislocations in a heteroepitaxial semiconductor structu | 438/363 | 438/413 438/495 |
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| 8 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5883911 A | 19990316 | 7 | Surface-emitting laser device | 372/45 | 372/96 |
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| 10 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5856206 A | 19990105 | 6 | Method for fabricating bragg reflector using in situ laser reflectometry | 438/32 | 118/715 438/29 |